Electronic Supplementary Information

High Performance, Low-Voltage Organic Field-Effect Transistors

Using Thieno[3,2-b]thiophene and Benzothiadiazole Co-Polymers

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- 1. Materials
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- 4. **OFET Fabrications**

1. Materials

All reagents were purchased from Aldrich, Merck and Acros Organics and used without further purification. All solvents used in the syntheses were of technical grade and freshly distilled prior to use. The solvents used in spectroscopic measurements were of spectroscopic grade. Synthesized compounds were purified by column chromatography using a Merck Silica Gel (0.015–0.040 mesh) as the adsorbent (stationary phase) packed into a glass column. Commercial TLC (Merck TLC Silica Gel 60 F254) was used for the determination of the extent of reaction as well as to find out the eluent (mobile phase) for the column chromatography.

2. Methods

2.1. Chemical structure confirmation:

¹H NMR and ¹³C NMR spectra of polymers were measured in deuterated chloroform with a Varian 500 and 125 MHz spectrometer, respectively using trimethylsilane, TMS as an internal standard. Proton and carbon chemical shifts were reported in parts per million (ppm).

2.2. Photophysical properties

UV measurements were recorded on HITACHI U-0080D. Fluorescence spectra were measured on HITACHI F-4500 Fluorescence Spectrophotometer.

2.3. Thermal properties

Thermalgravimetric analysis (TGA) as performed on PerkinElmer Diamond TA/TGA with a

heating rate of 10 °C min ⁻¹ under a nitrogen flow.

2.4. Electrochemical measurements

Cyclic voltammetry was performed using a CH-Instruments Model 400A electrochemical analyzer. Electrodes were used Pt wire as a working and counter, and an Ag reference electrode. The supporting electrolyte was $0.1 \text{ M Bu}_4\text{NPF}_6$ in ACN in all the measurements (**Fig. S1**).



Figure S1. Cyclic voltammograms of polymers P1, P2, P3 and P4

2.5. Determination of the molecular weights

Mass spectra (HRMS) of the monomers were recorded on Thermo LCQ-Deca ion trap mass instruments. The molecular weights of newly synthesized co-polymers were determined using a TOSOH EcoGPC system equipped with an auto sampler unit, a column oven, a temperature-controlled pump, a purge and degasser unit, and a TSK gel superhZ2000 column with 4.6 mm ID $\times 15$ cm $\times 2$ cm dimensions. THF was used as the eluent at the flow rate of 10 Ml min⁻¹ at 40 °C. A refractive index (RI) detector calibrated with polystyrene standard was used for the measurements. GPC data were analyzed using Eco-GPC Analysis software (**Fig. S2-S5**).

Result of molecular weight calculation (RI) Peak 1 Base Peak

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	[min]	[mV]	[mol]	Mn	4,085
Peak start	7.638	4.263	26,255	Mw	6,619
Peak top	8.670	19.055	3,214	Mz	11,261
Peak end	9.018	21.002	1,556	Mz+1	15,361
				Mv	6,619
Height [mV]			2.278	Mp	3,214
Area [mV*sec]			72.927	Mz/Mw	1.701
Height% [%]			1.939	Mw/Mn	1.620
[eta]			6618.66570	Mz+1/Mw	2.321

Figure S2: GPC result of P1

Result of molecular weight calculation (RI)

Peak 1	Rase	Peak
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	[min]	[mV]	[mol]	Mn	4,491
Peak start	7.662	4.783	25,059	Mw	6,897
Peak top	8.598	13.724	3,727	Mz	11,137
Peak end	8.922	14.781	1,905	Mz+1	15,102
				Mv	6,897
Height [mV]			1.509	Mp	3,728
Area [mV*sec]			50.218	Mz/Mw	1.615
Height% [%]			3.039	Mw/Mn	1.536
[eta]			6897.17619	Mz+1/Mw	2.190

Figure S3: GPC result of P2

Result of molecular weight calculation (RI)

Peak 1 Base Peak

	[min]	[mV]	[mol]	Mn	5,258
Peak start	7.657	2.147	25,311	Mw	7,336
Peak top	8.520	24.446	4,381	Mz	10,051
Peak end	8.955	70.297	1,777	Mz+1	12,734
				Mv	7,336
Height [mV]			23.018	Mp	4,774
Area [mV*sec]			1171.533	Mz/Mw	1.370
Height% [%]			100.000	Mw/Mn	1.395
[eta]			7335.54538	Mz+1/Mw	1.736

Figure S4: GPC result of P3

Result of molecular weight calculation (RI)

Peak 1	Base Peak	
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	[min]	[mV]	[mol]	Mn	8,664
Peak start	7.413	2.220	41,069	Mw	14,835
Peak top	7.678	8.314	24,237	Mz	21,388
Peak end	8.877	64.290	2,092	Mz+1	25,591
				Μv	14,835
Height [mV]			5.146	Мр	24,238
Area [mV*sec]			236.759	Mz/Mw	1.442
Height% [%]			7.065	Mw/Mn	1.712
[eta]			14834.82084	Mz+1/Mw	1.725

Figure S5: GPC result of P4

3. NMR Spectra



Figure S6. ¹H NMR of M3



Figure S7. ¹³C NMR of M3



Figure S8. ¹H NMR M4



Figure S9. ¹³C NMR of M4.

4. Mass Spectra



m/z	Theo. Mass	Delta (ppm)	RDB equiv.	Composition
380.87946	380.89764	-47.74	4.5	$C_{12}H_{15}Br_2S_2$

Figure S10. HRMS Spectra of M3



m/z	Theo. Mass	Delta (ppm)	RDB equiv.	Composition
423.95242	423.93341	-44.84	4.0	$C_{15}H_{21}Br_2S_2$

Figure S11. HRMS Spectra of M4

5. Organic Field-Effect Transistors

The structure of the fabricated bottom-gate, top-contact (BGTC) OFET and the chemical structure of CEC are depicted in **Fig. 5**. OFETs were fabricated by firstly a 100 nm thick aluminum layer was thermally evaporated to serve as the bottom gate electrode (Fig. S12a) onto a pre-washed corning glass substrate. To enable low-voltage operation of OFETs, cyanoethyl cellulose (CEC) with a high dielectric constant ($k \sim 14$) and low values of dielectric loss compared to other common organic insulating polymers^{1,2} is used as the dielectric thin film. When compared with poly(vinylidene fluoride) and its copolymers, CEC has good heat and acid stability, low moisture uptake and is mechanically robust. Most recently, Faraji *et al.* reported low-voltage operating

OFETs using solution-deposited, high-k gate dielectric layers based on nanocomposites of cyanoethylated cellulose (CEC) and barium strontium titanate (BST).³ CEC shavings purchased from Sigma Aldrich was dissolved in N,N-dimethylformamide (DMF) at 5 wt% and stirred for 3 h at room temperature until a homogenous solution was obtained. The solution was then filtered through 0.45mm PTFE membrane and spin-coated at 3000 rpm onto the gate electrode. The dielectric layer was then annealed at 90 °C for 90 min to form a solid, robust thin film. The thickness (d) of the CEC thin film measured using a DEKTAK 3ST profilometer was 280 ± 1 nm. The dielectric properties of the CEC layer were determined by the fabrication of parallel-plate capacitors. The capacitance per unit area (C_i) was measured 40 ± 2 Nf/cm² using an Agilent E4980A Precision LCR Meter in frequency range of 100 Hz-1 MHz. The dielectric constant (k) was calculated based on $Ci = \varepsilon_0 k/d$ as 13 ± 1 . Subsequently, to complete the OFET design, a prepared solution of each thienothiophene-based (TT) OSC in chloroform was spin-coated at 2000 rpm for 2 min on top the gate dielectric layer and annealed at 90 °C for 60 min. Finally, gold source and drain electrodes (~50 nm) were deposited through a shadow mask (Fig. S12b) by thermal evaporation. A typical substrate, consisting of 20 identical BGTC OFETs, fabricated in this work is illustrated in (Fig. S12c). The transistor characterisation was performed in ambient conditions (air with 40%-50% relative humidity) using an Agilent E5270B measurement mainframe with Karl Suss PH100 micromanipulator probes.



Fig. S12. (a) Gate and (b) source/drain electrodes shadow mask designs and dimensions and (c) a typical substrate consisting of 20 identical BGTC OFETs fabricated in this work



Fig. S13a-d. P1-P4 OFETs' subthreshold swing statistics obtained from at least 30 devices.

References

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